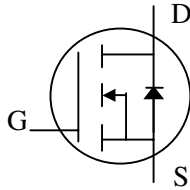




N-channel Enhancement-mode Power MOSFET

- Simple Drive Requirement**
- Low On-resistance**
- Fast Switching Performance**
- RoHS-compliant, halogen-free**

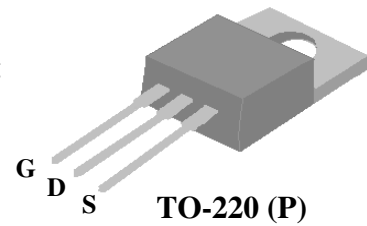


BV_{DSS}	120V
$R_{DS(ON)}$	8.5mΩ
I_D	130A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The AP92T12GP-HF-3 is in the TO-220 through-hole package which is used where a low PCB footprint or an attached heatsink is required.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	120	V
V_{GS}	Gate-Source Voltage	±20	V
I_D at $T_C=25^\circ C$	Continuous Drain Current (Chip)	130	A
I_D at $T_C=25^\circ C$	Continuous Drain Current ³	120	A
I_D at $T_C=100^\circ C$	Continuous Drain Current	95	A
I_{DM}	Pulsed Drain Current ¹	300	A
P_D at $T_C=25^\circ C$	Total Power Dissipation	375	W
P_D at $T_A=25^\circ C$	Total Power Dissipation	2	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	0.4	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	°C/W

Ordering Information

AP92T12GP-HF-3TB RoHS-compliant halogen-free TO-220, shipped in tubes (50pcs/tube)



Electrical Specifications at $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	120	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=30A$	-	-	8.5	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	5	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=30A$	-	62	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=96V, V_{GS}=0V$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Q_g	Total Gate Charge ²	$I_D=30A$	-	97	155	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=96V$	-	27	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	48	-	nC
$t_{d(on)}$	Turn-on Delay Time ²	$V_{DS}=60V$	-	27	-	ns
t_r	Rise Time	$I_D=30A$	-	96	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	42	-	ns
t_f	Fall Time	$R_D=2\Omega$	-	60	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	4600	7360	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	800	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	260	-	pF
R_g	Gate Resistance	$f=1.0\text{MHz}$	-	2	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=30A, V_{GS}=0V$	-	-	1.3	V
t_{rr}	Reverse Recovery Time ²	$I_S=10A, V_{GS}=0V$	-	80	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	260	-	nC

Notes:

1. Pulse width limited by maximum junction temperature.
2. Pulse test
3. Package limitation current is 120A

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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Typical Electrical Characteristics

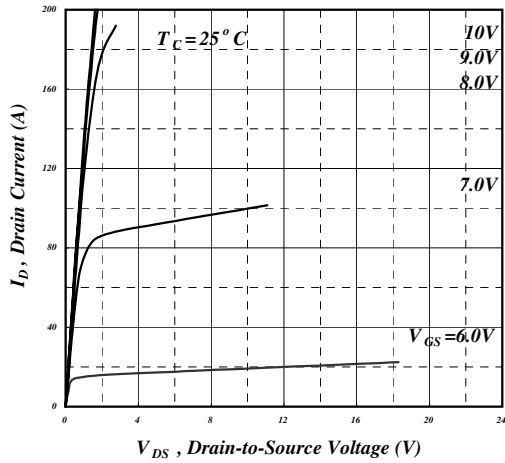


Fig 1. Typical Output Characteristics

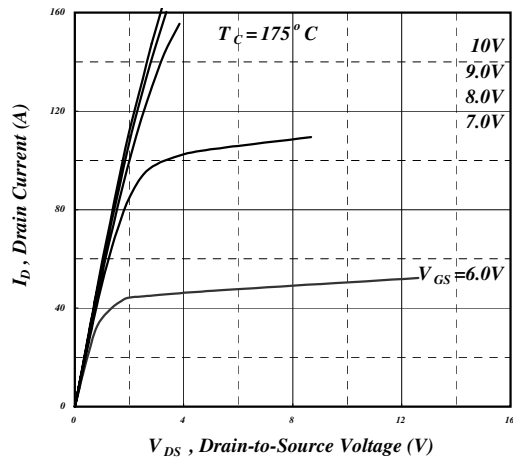


Fig 2. Typical Output Characteristics

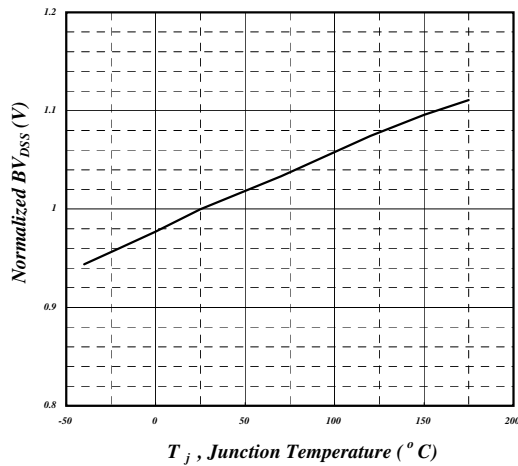


Fig 3. Normalized BVdss vs. Junction Temperature

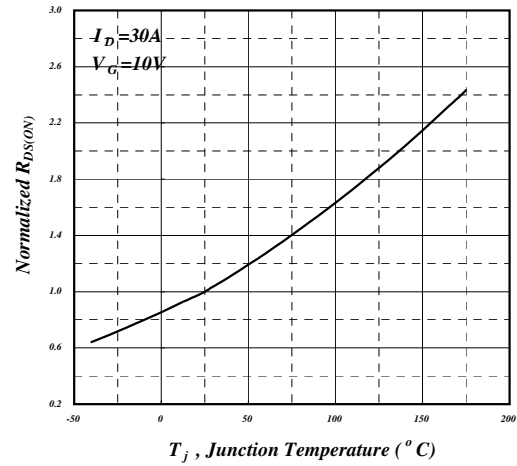


Fig 4. Normalized On-Resistance vs. Junction Temperature

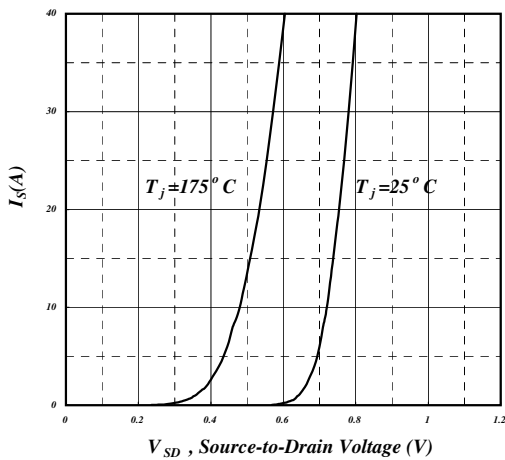


Fig 5. Forward Characteristic of Reverse Diode

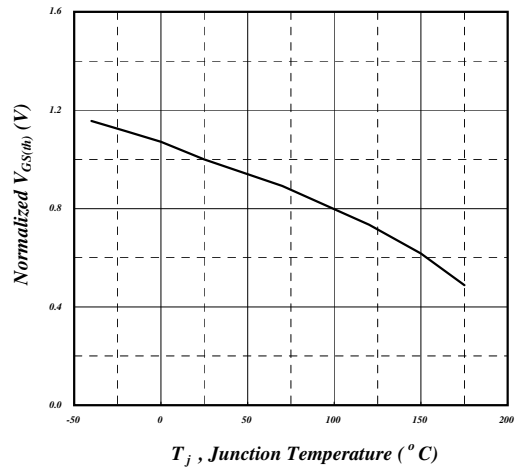


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



Typical Electrical Characteristics (cont.)

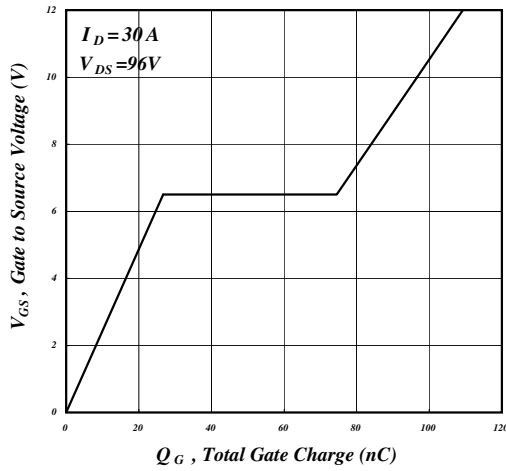


Fig 7. Gate Charge Characteristics

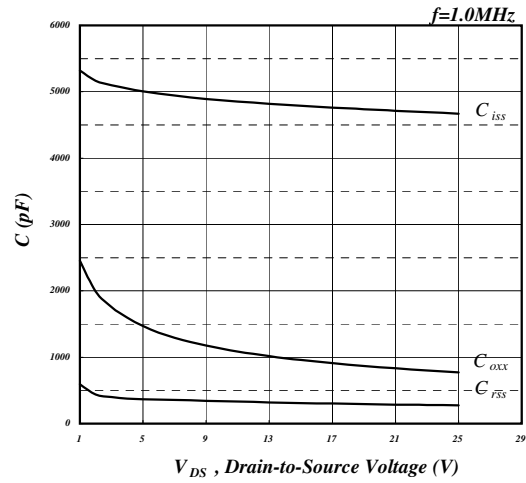


Fig 8. Typical Capacitance Characteristics

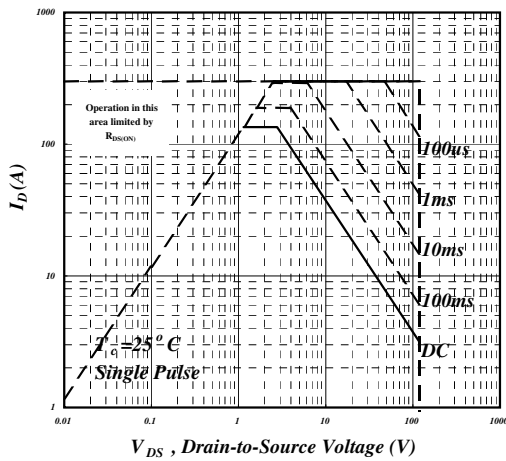


Fig 9. Maximum Safe Operating Area

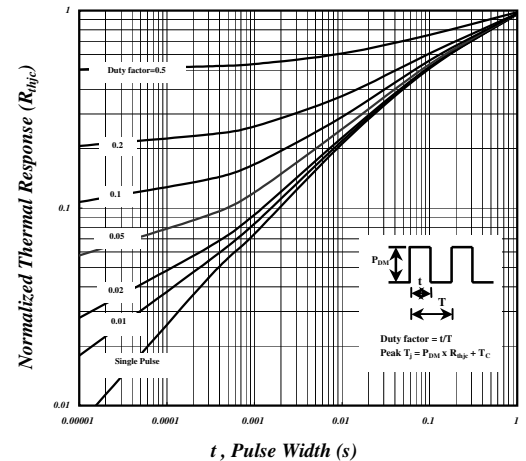


Fig 10. Effective Transient Thermal Impedance

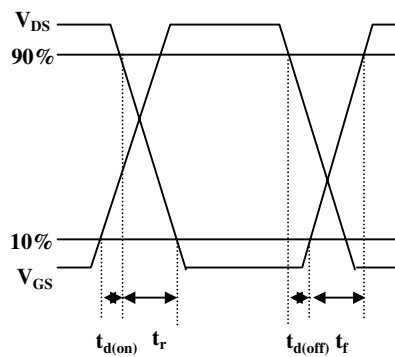


Fig 11. Switching Time Waveform

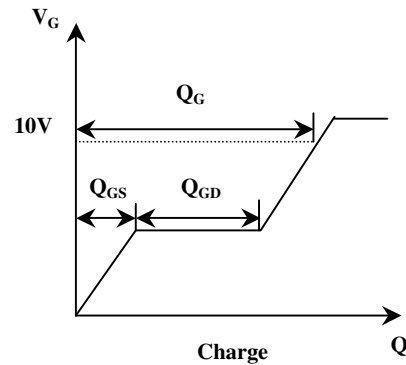


Fig 12. Gate Charge Waveform

